

Application No.: 10/812,880

AMENDMENT TO THE CLAIMS

1-11. (Cancelled)

12. (Currently amended) A semiconductor device comprising:

an insulating film;

an interconnect made of a first conductive film and a second conductive film that are stacked in sequence from the interconnect underside on the insulating film;

on the insulating film, a capacitor composed of:

a lower capacitor electrode made of the first conductive film;

a dielectric film formed on the lower capacitor electrode; and

an upper capacitor electrode made of the second conductive film and formed on the dielectric film,

wherein each of the lower capacitor electrode, the dielectric film, and the upper capacitor electrode has a same pattern; and

lower contacts are formed in the insulating film on ~~[[the]]~~ a bottom surface of the lower capacitor electrode, the lower contacts being connected to the lower capacitor electrode.

13. (Previously presented) The semiconductor device of Claim 12, wherein

a lower insulating film is formed beneath the insulating film;

a lower interconnect is formed on the lower insulating film; and

the lower contacts are connected to the lower interconnect.

Application No.: 10/812,880

14. (Previously presented) The semiconductor device of Claim 12, wherein a surface of the insulating film on which the capacitor is formed is planarized.

15. (Currently amended) The semiconductor device of Claim 13, wherein an upper insulating film is formed so as to cover the capacitor and the interconnect; and upper contacts are formed in the upper insulating film on ~~[[the]]~~ an upper surface of the upper capacitor electrode, the upper contacts being connected to the upper capacitor electrode.

16. (Previously presented) The semiconductor device of Claim 15, wherein an upper interconnect is formed on the upper insulating film; and the upper contacts are connected with the upper interconnect.

17. (Previously presented) The semiconductor device of Claim 12, wherein the first conductive film is made of a metal nitride.

18. (Previously presented) The semiconductor device of Claim 17, wherein the dielectric film is SiN.

19. (Previously presented) The semiconductor device of Claim 18, wherein the second conductive film is made of an aluminum alloy.